TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

# **TA8272H**

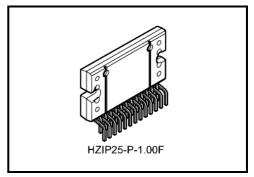
#### Max Power 43 W BTL × 4 ch Audio Power IC

The TA8272H is 4 ch BTL audio power amplifier for car audio application.

This IC can generate more high power: POUTMAX = 43~W as it is included the pure complementary PNP and NPN transistor output stage.

It is designed low distortion ratio for 4 ch BTL audio power amplifier, built-in stand-by function, muting function, and diagnosis circuit which can detect output to VCC/GND short, output offset voltage and over voltage input mode.

Additionally, the AUX amplifier and various kind of protector for car audio use is built-in.



Weight: 7.7 g (typ.)

#### **Features**

- High power: POUTMAX (1) = 43 W (typ.)
  - $(V_{CC} = 14.4 \text{ V}, f = 1 \text{ kHz}, \text{JEITA max}, R_L = 4 \Omega)$
  - : POUTMAX (2) = 40 W (typ.)
    - $(V_{CC} = 13.7 \text{ V}, f = 1 \text{ kHz}, \text{JEITA max}, R_L = 4 \Omega)$
  - : POUT(1) = 28 W (typ.)
  - $(V_{CC} = 14.4 \text{ V}, f = 1 \text{ kHz}, THD = 10\%, R_L = 4 \Omega)$
  - : POUT(2) = 24 W (typ.)
    - $(V_{CC} = 13.2 \text{ V}, f = 1 \text{ kHz}, THD = 10\%, R_L = 4 \Omega)$
- Built-in diagnosis circuit (pin 25)
- Low distortion ratio: THD = 0.02% (typ.)

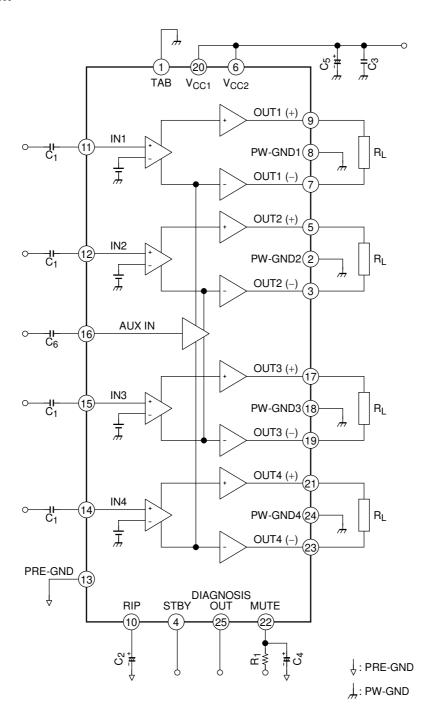
$$(V_{CC} = 13.2 \text{ V}, f = 1 \text{ kHz}, P_{OUT} = 5 \text{ W}, R_{L} = 4 \Omega)$$

• Low noise:  $V_{NO} = 0.10 \text{ mVrms (typ.)}$ 

(V<sub>CC</sub> = 13.2 V, 
$$R_g$$
 = 0  $\Omega$ ,  $G_V$  = 26dB,  $BW$  = 20 Hz~20 kHz)

- Built-in stand-by switch function (pin 4)
- Built-in muting function (pin 22)
- Built-in AUX amplifier from single input to 4 channels output (pin 16)
- Built-in various protection circuit
  - : Thermal shut down, over voltage, out to GND, out to VCC, out to out short
- Operating supply voltage: VCC (opr) = 9~18 V

## **Block Diagram**



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#### **Caution and Application Method**

(Description is made only on the single channel.)

#### 1. Voltage Gain Adjustment

This IC has no NF (negative feedback) terminals. Therefore, the voltage gain can't adjusted, but it makes the device a space and total costs saver.

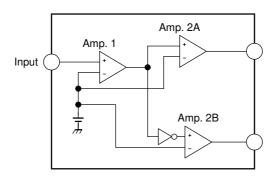


Figure 1 Block Diagram

The voltage gain of Amp.1:  $GV_1 = 0 dB$ The voltage gain of Amp.2A, B:  $GV_2 = 20 dB$ The voltage gain of BLT Connection: GV(BTL) = 6 dB

Therefore, the total voltage gain is decided by expression below.

 $GV = GV_1 + GV_2 + GV (BTL) = 0 + 20 + 6 = 26 dB$ 

#### 2. Stand-by SW Function (pin 4)

By means of controlling pin 4 (stand-by terminal) to high and low, the power supply can be set to ON and OFF. The threshold voltage of pin 4 is set at about 3VBE (typ.), and the power supply current is about 2  $\mu A$  (typ.) at the stand-by state.

## Control Voltage of pin 4: V<sub>SB</sub>

Stand-by	Power	V <sub>SB</sub> (V)
ON	OFF	0~1.5
OFF	ON	3~V <sub>CC</sub>

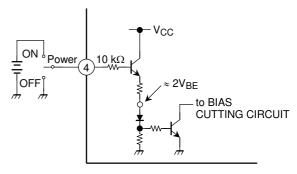


Figure 2 With pin 4 set to High, Power is turned ON

#### Adjustage of Stand-by SW

- (1) Since VCC can directly be controlled to ON or OFF by the microcomputer, the switching relay can be omitted.
- (2) Since the control current is microscopic, the switching relay of small current capacity is satisfactory for switching

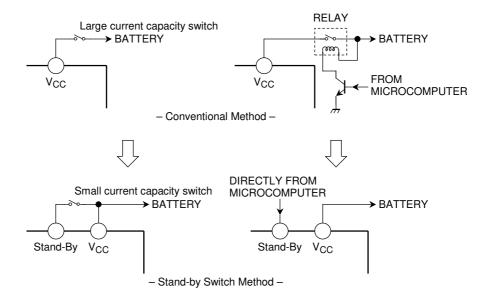


Figure 3

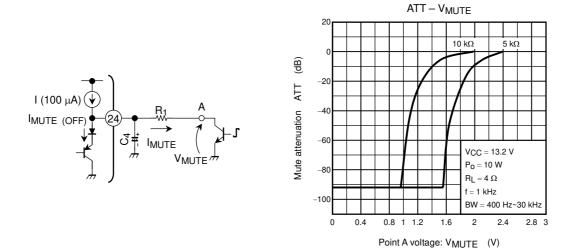
### 3. Muting Function (pin 22)

The muting time constant is decided by  $R_1$  and  $C_4$  and these parts is related the pop noise at power ON/OFF.

The series resistance;  $R_1$  must be set up less than 10 k $\Omega$ .

The muting function have to be controlled by a transistor, FET and  $\mu$ -COM port which has IMUTE > 250  $\mu$ A ability.

Terminal 22 must not be pulled up and it shall be controlled by OPEN/LOW.



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Figure 4 Muting Function

Figure 5 Mute Attenuation – V<sub>MUTE</sub> (V)

#### 4. AUX Input (pin 16)

The pin 16 is for input terminal of AUX amplifier.

The total gain is 0dB by using of AUX amplifier.

Therefore, the  $\mu\text{-}\mathrm{COM}$  can directly drive the AUX amplifier.

BEEP sound or voice synthesizer signal can be input to pin 16 directly.

When AUX function is not used, this pin must be connected to PRE-GND (pin 13) via a capacitor.

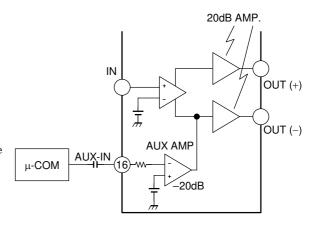
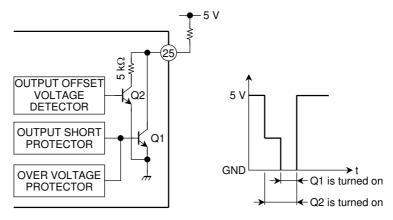


Figure 6 AUX Input

#### 5. Diagnosis Output (pin 25)

This diagnosis output terminal of pin 25 has open collector output structure on chip as shown in Figure 7. In case diagnosis circuit that detect unusual case is operated, NPN transistor (Q1) or (Q2) is turned on. It is possible to protect all the system of apparatus as well as power IC protection.

In case of being unused this function, use this IC as open-connection on pin 25.



pin 25: Open collector output (active low)

Figure 7 Self Diagnosis Output

#### 5.1 In Case of Shorting Output to V<sub>CC</sub>/GND or Over Voltage Power Supplied

NPN transistor (Q1) is turned on.

Threshold of over voltage protection: VCC = 22 V (typ.)

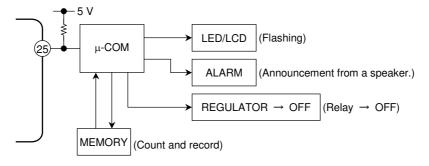


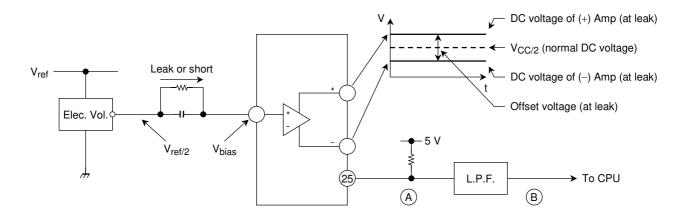
Figure 8 Application 1

#### 5.2 In Case of Shorting Output to Output

NPN transistor (Q1) is turned on and off in response to the input signal voltage.

# 5.3 In Case of Appearing Output Offset Voltage by Generating a Large Leakage Current on the Input Capacitor etc.

NPN transistor (Q2) is turned on while the inverted output voltage level become less than the threshold level of output offset voltage detector.



<sup>\*:</sup> It is possible to detect the abnormal output offset which is appeared by the large leakage of the input capacitor at  $V_{ref/2} > V_{bias}$  (about 1.4 V)

Figure 9 Application and Detection Mechanism

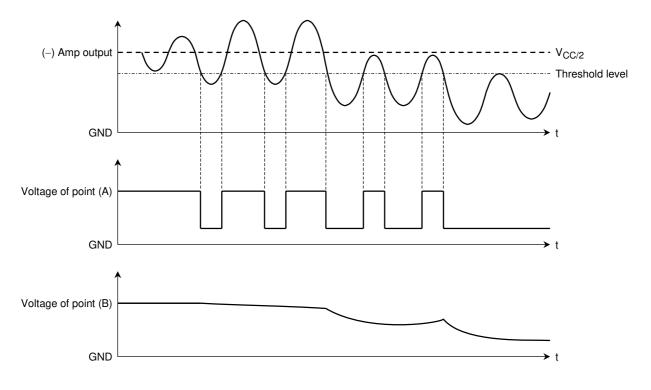


Figure 10 Wave Form

### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit	
Peak supply voltage (0.2 s)	V <sub>CC</sub> (surge)	50	V	
DC supply voltage	V <sub>CC (DC)</sub>	25	V	
Operation supply voltage	V <sub>CC (opr)</sub>	18	V	
Output current (peak)	I <sub>O (peak)</sub>	9	Α	
Power dissipation	P <sub>D</sub> (Note1)	125	W	
Operation temperature	T <sub>opr</sub>	-40~85	°C	
Storage temperature	T <sub>stg</sub>	-55~150	°C	

Note1: Package thermal resistance  $\theta_{j-T} = 1^{\circ}C/W$  (typ.) (Ta = 25°C, with infinite heat sink)

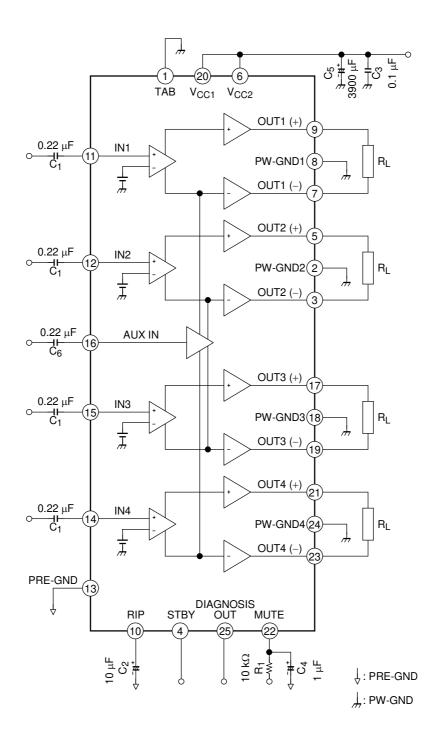
# Electrical Characteristics (unless otherwise specified $V_{CC}$ = 13.2 V, f = 1 kHz, $R_L$ = 4 $\Omega$ , Ta = 25°C)

		T					
Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Quiescent current	I <sub>CCQ</sub>	_	$V_{IN} = 0$	_	200	400	mA
Output power	P <sub>OUT</sub> MAX (1)	_	V <sub>CC</sub> = 14.4 V, max Power	_	43	_	w
	P <sub>OUT</sub> MAX (2)	_	V <sub>CC</sub> = 13.7 V, max Power	_	40	_	
	P <sub>OUT</sub> (1)	_	V <sub>CC</sub> = 14.4 V, THD = 10%	_	28	_	
	P <sub>OUT</sub> (2)	_	THD = 10%	22	24	_	
Total harmonic distortion	THD	_	P <sub>OUT</sub> = 5 W	_	0.02	0.2	%
Voltage gain	G <sub>V</sub>	_	V <sub>OUT</sub> = 0.775 Vrms (0dBm)	24	26	28	- dB
Voltage gain ratio	ΔG <sub>V</sub>	_	V <sub>OUT</sub> = 0.775 Vrms (0dBm)	-1.0	0	1.0	
Output noise voltage	V <sub>NO</sub> (1)	_	Rg = 0 Ω, DIN45405	_	0.12	_	mVrms
	V <sub>NO</sub> (2)	_	Rg = 0 Ω, BW = 20 Hz~20 kHz	_	0.10	0.35	
Ripple rejection ratio	R.R.	_	$f_{rip} = 100 \; Hz, \; Rg = 620 \; \Omega \ V_{rip} = 0.775 \; Vrms \; (0dBm)$	40	50	_	dB
Cross talk	C.T.	_	$\label{eq:reg_reg} \begin{split} & \text{Rg} = 620~\Omega \\ & \text{V}_{OUT} = 0.775~\text{Vrms}~\text{(0dBm)} \end{split}$	_	65	_	dB
Output offset voltage	V <sub>OFFSET</sub>	_	_	-150	0	150	mV
Input resistance	R <sub>IN</sub>	_	_	_	90	_	kΩ
Stand-by current	I <sub>SB</sub>	_	Stand-by condition	_	2	10	μА
Stand-by control voltage	V <sub>SB</sub> H	_	Power: ON	3.0	_	$V_{CC}$	V
	V <sub>SB</sub> L	_	Power: OFF	0	_	1.5	
Mute control voltage (Note2)	V <sub>M</sub> H	_	Mute: OFF	Open			_
	V <sub>M</sub> L	_	Mute: ON, $R_1 = 10 \text{ k}\Omega$	0		0.5	V
Mute attenuation	ATT M	_	Mute: ON, V <sub>OUT</sub> = 7.75 Vrms (20dBm) at Mute: OFF.	80	90	_	dB

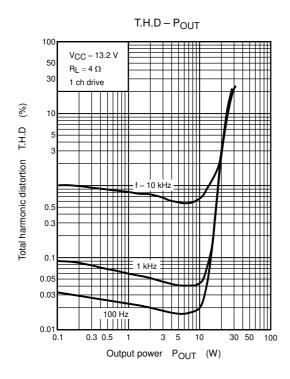
Note2: Muting function have to be controlled by open and low logic, which logic is a transistor, FET and  $\mu$ -COM port of  $I_{MUTE} > 250~\mu A$  ability.

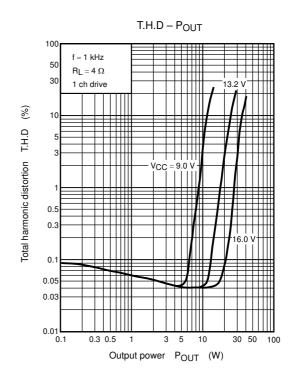
This means than the mute control terminal: pin 22 must not be pulled-up.

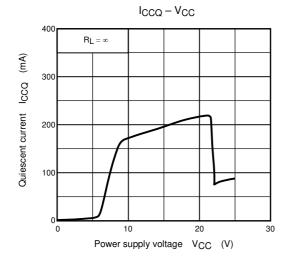
### **Test Circuit**

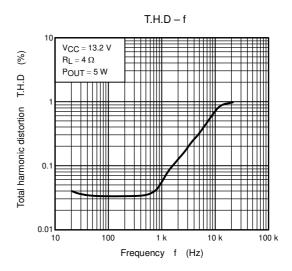


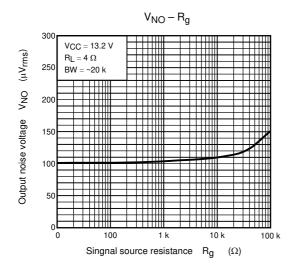
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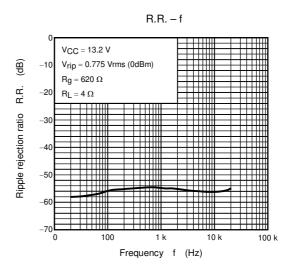


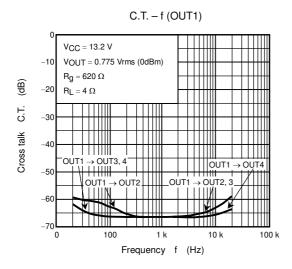


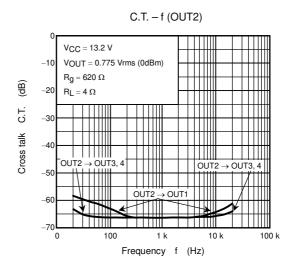


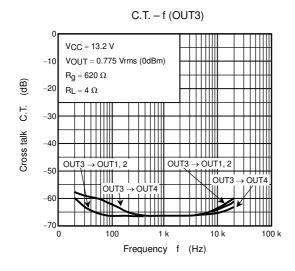


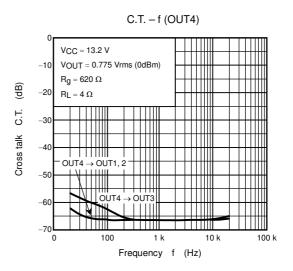


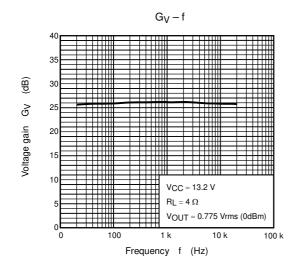


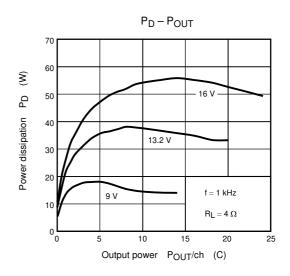


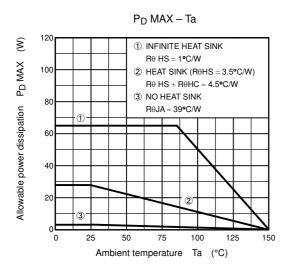








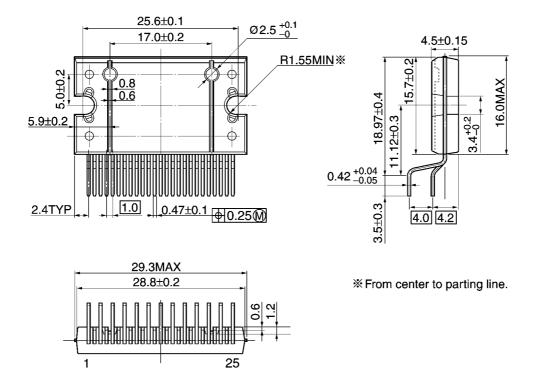




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## **Package Dimensions**

HZIP25-P-1.00F Unit: mm



Weight: 7.7 g (typ.)

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